



PTO/SB/08A (08-03)

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/666,034	
			Filing Date	September 18, 2003	
			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
Sheet	1	of	12	Examiner Name	Long Pham
				Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code ² (if known)			
LP	1	US-3,404,295	10-01-1968	Warner et al.	
	2	US-3,412,297	11-19-1968	Amlinger	
	3	US-3,497,777	02-24-1970	Teszner et al.	
	4	US-3,564,356	02-16-1971	Wilson	
	5	US-3,660,697	05-02-1972	Berglund et al.	
	6	US-4,003,072	01-11-1977	Matsushita et al.	
	7	US-4,300,150	11-10-1981	Colak	
	8	US-4,326,332	04-27-1982	Kenney et al.	
	9	US-4,337,474	06-29-1982	Yukimoto	
	10	US-4,345,265	08-17-1982	Blanchard	
	11	US-4,445,202	04-24-1984	Geotze et al.	
	12	US-4,579,621	04-01-1986	Hine	
	13	US-4,636,281	01-13-1987	Buiguez et al.	
	14	US-4,638,344	01-20-1987	Cardwell, Jr.	
	15	US-4,639,761	01-27-1987	Singer et al.	
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	17	US-4,716,126	12-29-1987	Cogan	
	18	US-4,746,630	05-24-1988	Hui et al.	
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	20	US-4,774,556	09-27-1988	Fujii et al.	
	21	US-4,801,986	01-31-1989	Chang et al.	
	22	US-4,821,095	04-11-1989	Temple	
	23	US-4,823,176	04-18-1989	Baliga et al.	
	24	US-4,853,345	08-01-1989	Himelick	
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	34	US-5,027,180	06-25-1991	Nishizawa et al.	
	35	US-5,034,785	07-23-1991	Blanchard	
	36	US-5,071,782	12-10-1991	Mori	
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	41	US-5,142,640	08-25-1992	Iwanatsu	

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U.S. PATENT DOCUMENTS+					
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LP	42	US-5,164,325	11-17-1992	Cogan et al.	
	43	US-5,164,802	11-17-1992	Jones et al.	
	44	US-5,216,275	06-01-1993	Chen	
	45	US-5,219,777	06-15-1993	Kang	
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	47	US-5,233,215	08-03-1993	Baliga	
	48	US-5,262,336	11-16-1993	Pike, Jr. et al.	
	49	US-5,268,311	12-07-1993	Euen et al.	
	50	US-5,275,965	01-04-1994	Manning	
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	53	US-5,300,447	04-05-1994	Anderson	
	54	US-5,326,711	07-05-1994	Malhi	
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	61	US-5,424,231	06-13-1995	Yang	
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	68	US-5,454,435	07-18-1995	Baliga	
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	84	US-5,597,765	01-28-1997	Yilmaz et al.	
	85	US-5,605,852	02-25-1997	Bencuya	
	86	US-5,616,945	04-01-1997	Williams	
	87	US-5,623,152	04-22-1997	Majumdar et al.	
	88	US-5,629,543	05-13-1997	Hshieh et al.	
	89	US-5,637,898	06-10-1997	Bailga	
	90	US-5,639,676	06-17-1997	Hshieh et al.	
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	96	US-5,689,128	11-18-1997	Hshieh et al.	
	97	US-5,693,569	12-02-1997	Ueno	
	98	US-5,705,409	01-06-1998	Witek	
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	100	US-5,714,781	02-03-1998	Yamamoto et al.	
	101	US-5,719,409	02-17-1998	Singh et al.	
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	104	US-5,776,813	07-07-1998	Huang et al.	
	105	US-5,780,343	07-14-1998	Bashir	
106	US-5,801,417	09-01-1998	Tsang et al.		
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108	US-5,877,528	03-02-1999	So		
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		Number Kind Code ² (* known)			
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	125	US-5,973,360	10-26-1999	Tihanyi	
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	136	US-6,034,415	05-07-2000	Johnson et al.	
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LP	165	US-6,168,983	01-02-2001	Rumennik et al.	
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	208	US-6,351,018	02-26-2002	Sapp	
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	218	US-6,376,878	04-23-2002	Kocon	
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246	US-2001/0028083 A1	10-11-2001	Onishi et al.		

Examiner Signature	Long Pham	Date Considered	7/22/05
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(use as many sheets as necessary)

Sheet	7
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of

12

Complete if Known

Application Number

10/666,034

Filing Date

September 18, 2003

First Named Inventor

Kocon, Christopher Boguslaw

Art Unit

2814

Examiner Name

Long Pham

Attorney Docket Number

018865-009010US

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ⁴ (if known)				
LP	259	CN	1036666A	10-25-1989			<input checked="" type="checkbox"/>
	260	DE	4300806 C1	12-23-1993	Siemens AG		<input checked="" type="checkbox"/>
	261	DE	19736981 A1	08-20-1998	Mitsubishi Denki		<input checked="" type="checkbox"/>
	262	EP	0747967 B1	02-27-2002	ST Microelectronics Inc.		<input type="checkbox"/>
	263	EP	0975024 A2	01-02-2000	Fuji Electric Co. LTD.		<input type="checkbox"/>
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	265	EP	1054451 A2	11-22-2000	Intersil Corporation		<input type="checkbox"/>
	266	EP	1205980 A1	05-15-2002	Infineon Technologies AG		<input type="checkbox"/>
	267	JP	01-192174 A	08-02-1989	Hitachi LTD.		<input checked="" type="checkbox"/>
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		Application Number	10/666,034		
		Filing Date	September 18, 2003		
		First Named Inventor	Kocon, Christopher Boguslaw		
		Art Unit	2814		
Examiner Name	Long Pham				
Sheet	8	of	12	Attorney Docket Number	018865-009010US

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	270	JP	62-069562		03-30-1987	Mitsubishi Electric Corp		<input checked="" type="checkbox"/>
	271	JP	63-186475		08-02-1988	Nissan Motor Co. LTD.		<input checked="" type="checkbox"/>
	272	JP	63-288047		11-25-1988	Toshiba Corp.		<input checked="" type="checkbox"/>
	273	JP	64-022051		01-25-1989	Matsushita Electric Ind		<input checked="" type="checkbox"/>
	274	JP	2000-040822		02-08-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	275	JP	2000-040872		02-08-2000	Senju Metal IND CO LTD.		<input checked="" type="checkbox"/>
	276	JP	2000-156978	A	06-06-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	277	JP	2000-277726	A	10-06-2000	Toshiba Corp.		<input checked="" type="checkbox"/>
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	279	JP	2001-015448		01-19-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	280	JP	2001-015752		01-19-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	281	JP	2001-102577	A	04-13-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	282	JP	2001-111041	A	04-20-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	283	JP	2001-135819	A	05-18-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	284	JP	2001-144292	A	05-25-2001	Denso Corp.		<input checked="" type="checkbox"/>
	285	JP	2001-244461	A	09-07-2001	Toyota Central Res & Dev Lab INC.		<input checked="" type="checkbox"/>
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	288	PCT	WO 00/33386	A2	06-08-2000	Koninklijke Philips Electronics		<input type="checkbox"/>
	289	PCT	WO 00/68997	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	290	PCT	WO 00/68998	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	291	PCT	WO 00/75965	A2	12-14-2000	General Semiconductor, Inc.		<input type="checkbox"/>
	292	PCT	WO 01/06550	A1	01-23-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	293	PCT	WO 01/06557	A1	01-25-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	294	PCT	WO 01/45155	A1	06-21-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	295	PCT	WO 01/59847	A2	08-16-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
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Examiner Signature	Long Pham	Date Considered	7/22/05
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60436135 v1

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	10/666,034
				Filing Date	September 18, 2003
				First Named Inventor	Kocon, Christopher Boguslaw
				Art Unit	2814
Examiner Name	Long Pham				
Sheet	9	of	12	Attorney Docket Number	018865-009010US

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
LP ↓	298	PCT	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>
	299	PCT	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation		<input type="checkbox"/>
	300	PCT	WO 02/047171	A1	06-13-2002	International Rectifier Corporation		<input type="checkbox"/>
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
LH	301	BAI et al., "Novel automated optimization of power MOSFET for 12V input, high-frequency DC-DC converter," <i>International Symposium on Power Semiconductors and ICs, Technical Digest</i> , (2003), pp. 366-369.	
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Examiner Signature	Long Pham	Date Considered	8/22/05
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		Examiner Name	Long Pham		
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LP	317	"IR develops CoolMOS™ -equivalent technology, positions it at the top of a 3-tiered line of new products for SMPS," International Rectifiers company information available at http://www.irf.com (1999) 3 pages total.	
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LP	333	Technical Literature from Quester Technology, Model APT-4300 300mm Atmospheric TEOS/Ozone CVD System, (unknown date), 3 pages total.	
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V	340	YAMASHITA et al., "Conduction Power loss in MOSFET synchronous rectifier with parallel-connected schottky barrier diode, (July 1998) <i>IEEE Transactions on Power electronics</i> , Vol. 13, No. 4, pp. 667-673.	

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